IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

REVOCATION OF POWER OF ATTORNEY

Assistant Commissioner for Patents Alexandria, VA 22313-1450

Dear Sir:

I am an officer of MACRONIX International Co., Ltd. authorized to act on behalf of MACRONIX International Co., Ltd., the assignee of the entire right, title and interest in the attached list of applications for patent. Evidences of these assignments are recorded in the Patent and Trademark Office as the enclosed list, Appendix A.

. I hereby revoke all previous powers of attorney to prosecute these applications and to transact all business connected therewith.

POWER OF ATTONEY

As an officer of the assignee of the entire right, title and interest in the above-referenced application for patent, I hereby appoint the following attorney(s) and/or Agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith:

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CHIH YUAN LU

President

MACRONIX International Co., Ltd.

	Attorney Docket No.	TITLE	Filing Date	Appl. No.	Reel No.	Frame No.
		METHOD FOR ELININATIONG POLYCIDE VOIDS THROUGH				
_	10311-US-PA	NITROGEN IMPLANTATION	2005/1/28	11/044,212	016047	9290
2	10496-US-PA	PVCS (PEER VERSION CONTROL SYSTEM)	2003/6/23	10/600700	014223	0556
3	11064-US-PA	CLEANING METHOD USING OZONE DI PROCESS	2003/12/10	10/731150	014785	0392
		APPARATUS AND METHOD TO IMPROVE THE ERASE UNIFORMITY				
		AND TEST MODE TO SCREEN MARGINAL CELLS IN AN NROM				
4	14744-US-PA	MEMORY ARRAY	2005/4/1	11/096,878	016092	1920
		OPERATION METHODS FOR A NON-VOLATILE MEMORY CELL IN AN				
5	14994-US-PA	ARRAY	2007/9/17	11/856,457	016359	0831
9	15319-US-PA	METHOD OF FORMING ONO FOR NITRIDE FLASH MEMORY	2005/11/15	11/274,781	017235	0285
7	15319-US-PA-1	METHOD OF FORMING ONO FOR NITRIDE FLASH MEMORY	2007/9/19	11/964,322	017235	0285
		METHOD TO FORM ONO AND DIFFUSION BIT LINES FOR NITRIDE				
8	15706-US-PA	NON-VOLATILE MEMORY	2005/8/23	11/209,875	017162	9920
6	15720-US-PA	THREE-DIMENSIONAL MEMORY DEVICES	2006/3/21	11/385,360	017832	6890
		METHODS OF TRENCH AND CONTACT FORMATION IN MEMORY		-		
01	15937-US-PA	CELLS	2006/7/26	11/459,990	018386	0511



	Attorney Docket No.	TITLE	Filing Date	Appl. No.	Reel No.	Frame No.
		A PARTIAL SILICON-ON-INSULATOR STRUCTURE AND ITS				
=	15954-US-PA	FABRICATION METHOD	2006/5/18	11/383,973	018038	7620
		NON-VOLATILE MEMORY CELLS AND METHODS OF				
12	15962-US-PA	MANUFACTURING THE SAME	2005/8/4	11/197,659	016520	0672
13	15963-US-PA	DIODE-LESS ARRAY FOR ONE-TIME PROGRAMMABLE MEMORY	2005/12/8	11/297,529	018067	0737
		METHOD OF MANUFACTURING DUAL GATE MULTI-BIT				
		SEMICONDUCTOR MEMORY BY USING POLYMER SHRINKED			· · · · · · · · · · · · · · · · · · ·	
14	16279-US-PA	NANO-SPACE	2006/2/13	11/352,788	019284	9620
15	16343-US-PA	A METHOD TO PRODUCE HIGH VOLTAGE DEVICE	2005/12/16	11/303.176	017368	0066
91	16646-US-PA	DUAL GATE MULTI-BIT SEMICONDUCTOR MEMORY	2006/2/17	11/356,659	017481	0965
17	17610-US-PA	METHOD OF RESOLUTION IMPROVEMENT	2006/6/5	11/422,284	018060	0504
		PATTERN REGISTRATION MARK DESIGNS FOR USE IN				
18	17845-US-PA	PHOTOLITHOGRAPHY AND METHODS OF USING THE SAME	2006/4/25	11/410,424	017837	0553
19	19109-US-PA	A SYSTEM FOR OPERATING A MEMORY DEVICE	2008/3/21	12/053,411	020686	0153
20	20 19110-US-PA	DECODING METHOD IN AN NROM FLASH MEMORY ARRAY	2006/9/25	11/534,696		

	Attorney Docket No:	Title	Filing Daté	Appl. No.	Reel No.	Frame No.
		A Semiconductor Structure And Process For Reducing The Second Bit Effect Of		entrant de la companya de la company	Condest in Management & Country of the Condest	
21	19681-US-PA	A Memory Device	2007/4/10	11/786,078	019446	0496
22	21044-US-PA	A Method To Increase Gcr Of Virtual Ground Floating Gate Flash Memories	2006/5/12	11/383,073	017611	0588
23	21247-US-PA	Structure Of Magnetic Random Access Memory Using Spin-Torque Transfer Writing And Method For Manufacturing Same	2006/12/1	11/607 612	018734	0110
		Cell Operation Methods Using Gate-Injection For Floating Gate Nand Flash				
24	21370-US-PA	Memory	2006/10/3	11/542,749	018651	0598
25	21566-US-PA	Side Lobe Image Searching Method In Lithography	2006/12/28	11/647,068	918885	0386
96	\$1567-115.P&	Spatial Energy Distribution By Slit Filter For Step-And-Scan System On Multiple Foots Exposure	7/1/2000	0177011	0.000	0000
2	4120-10C14	Multiple rocus Exposure	200 // 1/4	11/049,5 /0	020122	0770
27	21706-US-PA	Resistance Random Access Memory	2007/1/19	11/656,246	019032	0600
		A Non-Volatile Semiconductor Memory Device And A Method Of Fabricating				
28	21707-US-PA	A Nonvolatile Semiconductor Memory Device	2007/3/30	11/693,716	019095	0943
		Inverted T-Shaped Floating Gate Memory And Method For Fabricating The				
29	21830-US-PA	Same	2008/2/22	12/036,196	020553	0422
		Method Of Programming And Erasing A P-Channel Be-Sonos Nand Flash				
30	27491-US-PA	Memory	2006/5/5	11/381,760	017981	0223

	Attorney Docket No.	TITLE	Filing Date	Appl. Nö.	Reel No.	Frame No.
		LOADING DATA WITH ERROR DETECTION IN A POWER ON				Control of the Contro
31	27645-US-PA	SEQUENCE OF FLASH MEMORY DEVICE	2006/10/5	11/538,844	018872	0505
_		NEURAL NETWORK FOR DETERMINING AN ENDPOINT IN AN ETCH				
32	27826-US-PA-0C	PROCESS	2006/12/27	11/646,205	020713	0648
33	27829-US-PA	DOUBLE EXPOSURE APPLICATION	2004/12/22	11/017,684	016123	0255
		METHOD OF FORMING BOTTOM OXIDE FOR NITRIDE FLASH				
34	27830-US-PA	MEMORY	2005/9/27	11/235,786	016754	2060
35	27831-US-PA	ASYMMETRIC FLOATING GATE NAND FLASH MEMORY	2005/8/23	11/209,437	020871	0561
36	27832-US-PA	LOW-K SPACER STRUCTURE FOR THE FLASH MEMORY	2007/11/9	11/943,888	016826	2290
37	37 27833-US-PA	THE REFERENCE CELLS AUTO TRIMMING	2005/11/10	11/271,300	016968	0287
		LAYOUT OF WORD LINE DRIVER WIDTH IS PERPENDICULAR TO				
38	27834-US-PA	ARRAY WORD LINE	2005/5/25	11/137,098	016292	0235
		A NOVEL DOPING PROFILE TO IMPROVE THE INTEGRITY OF TWIN				
39	27835-US-PA	BIT CELL FLASH MEMORY	2005/8/22	11/209,145	017370	0912
40	27836-US-PA	MAP (MOBILE AUDIO PLATFORM) SYSTEM ARCHITECTURE	2005/9/15	11/227,380	016859	0311

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		METHOD OF FORMING AND OPERATING AN ASSISTED CHARGED			0.1.00.1	ramo NO.
41	27837-US-PA	NITRIDE-TRAP MEMORY DEVICE	2005/12/2	11/292,024	017249	0736
		NEGATIVE CHARGE-PUMP WITH CIRCUIT TO ELIMINATE PARASITIC				
42	27838-US-PA	DIODE TURN-ON	2005/9/23	11/233,901	016775	0633
		A LAYER DECODING SCHEME AND STRUCTURE FOR 3				
43	27839-US-PA	DIMENSIONAL MEMORY	2006/3/21	11/385,061	017568	0352
44	27840-US-PA	MAP (MOBILE AUDIO PLATFORM) DOWNLOAD SCHEME	2005/9/15	11/226,987	016838	0129
45	27841-US-PA	BACKGROUND SOUND MIXER	2005/9/15	11/227,621	016842	0445
		INTERFACE FOR A REMOVABLE ELECTRONIC DEVICE AND METHOD				
46	46 27842-US-PA	THEREOF	2005/9/15	11/227,622	016838	0554
47	27843-US-PA	METHOD FOR REFRESHING A FLASH MEMORY	2006/6/8	11/449,361	018152	0268
		METHODS OF ETCHING STACKS HAVING METAL LAYERS AND				
48	27844-US-PA	HARD MASK LAYERS	2006/5/9	11/382,401	017974	0192
		PLASMA ETCHING METHODS USING NITROGEN MEMORY SPECIES				
49	27845-US-PA	FOR SUSTAINING GLOW DISCHARGE	2006/2/22	11/359,787	017881	0520
50	50 27846-US-PA	PRESSURE CALIBRATION	2006/4/21	11/409,127	908/10	0648

7	Attorney Docket No	TITLE	Filing Date Appl. No.	Appl. No.	Reel No.	Frame No
		NON-VOLATILE MEMORY CELLS HAVING A				
		POLYSILICON-CONTAINING, MULTI-LAYER INSULATING STRUCTURE,				
		MEMORY ARRAYS INCLUDING THE SAME AND METHODS OF				
51 2	27847-US-PA	OPERATING THE SAME	2006/10/27	11/588,830	018730	0493
		NVM CELLS HAVING OXIDE/NITRIDE MULTI-LAYER INSULATING				
52 2	27848-US-PA	STRUCTURES AND METHODS OF OPERATING THE SAME	2007/1/3	11/649,348	019275	1990
		A HIGH SECOND BIT OPERATION WINDOW METHOD FOR NAND				
53 2	27850-US-PA	ARRAY WITH TWO-BIT MEMORY CELLS	2008/2/22	12/035,786	020548	8800
		METHOD OF IMPROVING OVERLAY PERFORMANCE IN				
54 2	27851-US-PA	SEMICONDUCTOR MANUFACTURE	2006/12/11	11/636,927	018707	0922
55 2	27852-US-PA	FLASH MEMORY ARRAY ARCHITECTURE	2008/1/4	11/969,812	020203	0987
56	27853-US-PA	PROGRAMMING SCHEME FOR NON-VOLATILE FLASH MEMORY	2006/12/11	11/636,920	018833	0415
57 2	27854-US-PA	MEMORY SYSTEM AND A VOLTAGE REGULATOR	2007/3/30	11/693,712	019088	0615
		FLASH MEMORY WITH 4-BIT MEMORY CELL AND METHOD FOR				
58	27855-US-PA	FABRICATING THE SAME	2007/6/8	11/760,646	819610	1560
59	27856-US-PA	NON-VOLATILE MEMORY WITH IMPROVED ERASING OPERATION	2007/2/7	11/703,916	018983	0446
7 09	60 27857-US-PA	MEMORY CHIP WITH WRITE LOCK-DOWN FEATURE	2007/9/28	11/863,254	019893	6110

	Attorney Docket No.	IULE	Filing Date Appl. No.	Appl. No.	Reel No.	Frame No.
19	27858-US-PA	MULTI-LEVEL-CELL TRAPPING DRAM	2007/6/11	11/761,344	020285	0331
		INVERTED T-SHAPED FLOATING GATE MEMORY AND METHOD FOR				
62	27859-US-PA	FABRICATING THE SAME	2007/11/16 11/941,813	11/941,813	020128	0727
63	27861-US-PA	METHOD FOR PERFORMING OPERATIONS ON A MEMORY CELL	2007/11/22	11/945,181	020154	0578
		METHOD OF FABRICATING INTEGRATED CIRCUIT WITH SMALL				
64	64 27863-US-PA	PITCH	2007/8/29	11/846,900	019762	0485
		PATTERNING STRUCTURE AND METHOD FOR SEMICONDUCTOR				
65	27864-US-PA	DEVICES	2007/11/21	11/943,900	020146	9/10
		A MASK FOR CONTROLLING LINE END SHORTENING AND CORNER				
99	27866-US-PA	ROUNDING ARISING FROM PROXIMITY EFFECTS	6/1/8002	11/971,900	020350	0108
29	21938-US-PA	MEMORY DEVICES	2008/6/13	12/139,418	021097	0746
		METHOD AND SYSTEM FOR MANUFACTRUING OPENING ON				
89	27867-US-PA	SEMICONDUCTOR DEVICES	2008/6/20	12/143,730	021132	0465
		TWO-BITS PER CELL NOT-AND GATE (NAND) NITRIDE TRAP				
69	69 28720-US-PA	MEMORY	2008/5/19	12/123,302	919910	0338